

RoHS

COMPLIANT HALOGEN

FREE

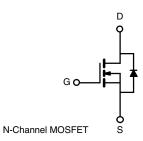
# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.006				
I <sub>D</sub> (A)	120				
Configuration	Single				
Package	TO-263				



### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified <sup>d</sup>
- 100 %  $\rm R_g$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \degree C$ , unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V <sub>DS</sub>	60	- V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
Continuous Drain Current	T <sub>C</sub> = 25 °C ª	I	120			
Continuous Drain Current	T <sub>C</sub> = 125 °C	ID	80			
Continuous Source Current (Diode Conductio	I <sub>S</sub>	120	А			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	480				
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	65			
Single Pulse Avalanche Energy	L = 0.1 IIIH	E <sub>AS</sub>	211	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Р	230	- w		
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	76	vv		
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.65	0/10		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

# SQM120N06-06



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static							1	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		60	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.0	3.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0045	0.0060		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0104	Ω	
		$V_{GS} = 10 V$	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0129		
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 30 A	-	94	-	S	
Dynamic <sup>b</sup>	<u>.</u>							
Input Capacitance	C <sub>iss</sub>			-	5196	6495		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	708	885	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	336	420		
Total Gate Charge <sup>c</sup>	Qg			-	96.5	145		
Gate-Source Charge	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 75 \text{ A}$	-	24.6	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>				27.2	-		
Gate Resistance	Rg		f = 1 MHz		1	1.7	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		$V_{DD} = 30 \text{ V}, \text{ R}_1 = 0.4 \Omega$		16	24	ns	
Rise Time <sup>c</sup>	tr	V <sub>DD</sub> =			14	21		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 75$ Å, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		-	34	51		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 75 A, V <sub>GS</sub> = 0		-	0.9	1.5	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

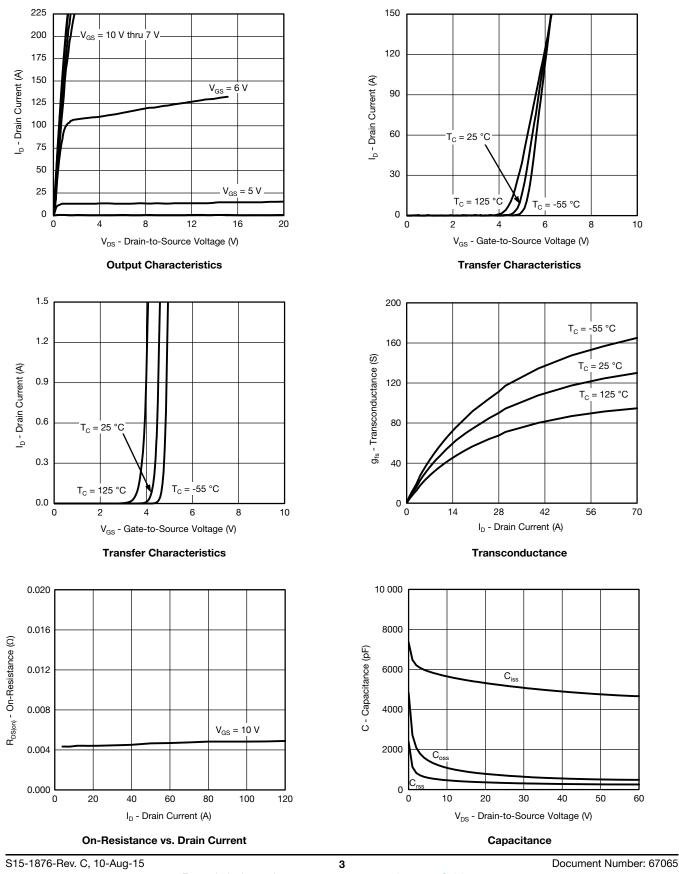
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



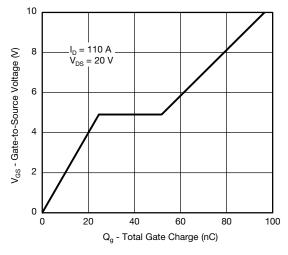
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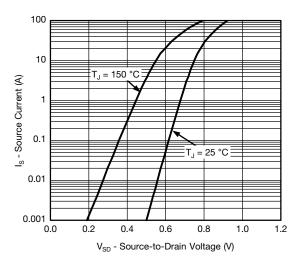
# SQM120N06-06

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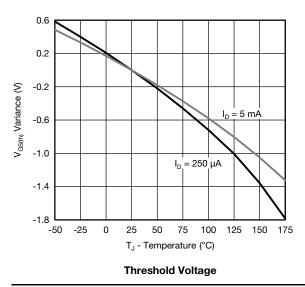
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

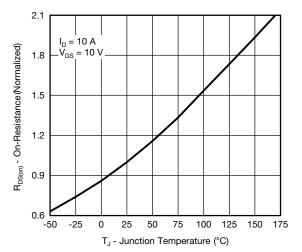


Gate Charge

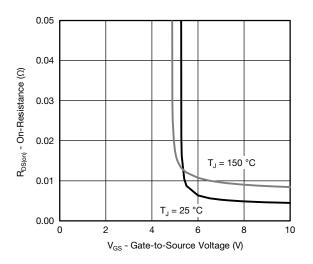


Source Drain Diode Forward Voltage

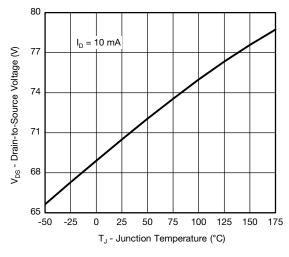




**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S15-1876-Rev. C, 10-Aug-15

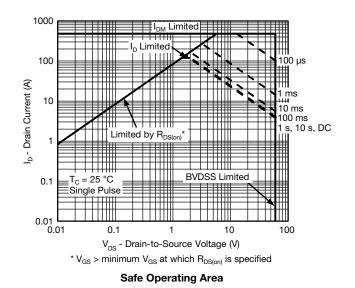
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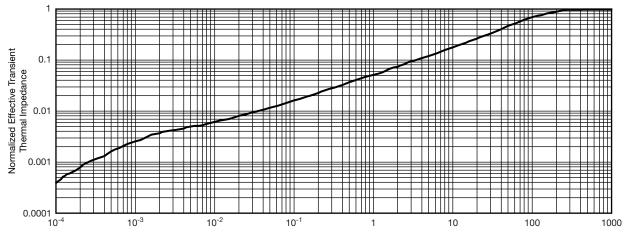
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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





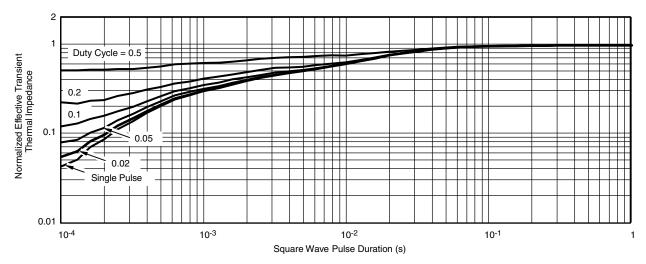
Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient





### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# SQM120N06-06

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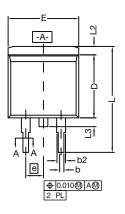
REVISION HISTORY <sup>a</sup>				
REVISION	DATE	DESCRIPTION OF CHANGE		
С	04-Aug-15	Revised R <sub>g</sub> minimum limit		

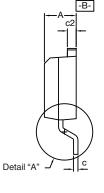
Note

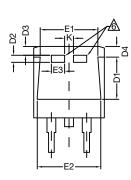
a. As of April 2014



TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INC	HES	MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
A		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.045 0.055		1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
С	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
E1		0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
е		0.100 BSC		2.54 BSC		
К		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25  $\,\%\,$  of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



## **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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